

V_{DSS}	-45V
$R_{DS(on)}$ (Max.)	190mΩ
I_D	-2.0A
P_D	1.0W

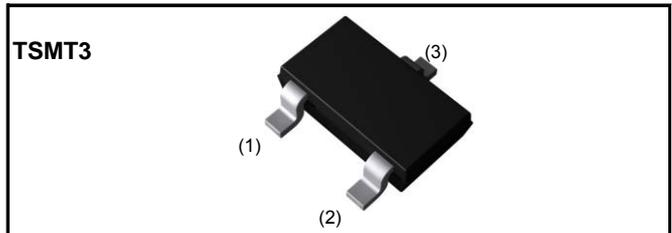
●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT3).
- 4) Pb-free lead plating ; RoHS compliant

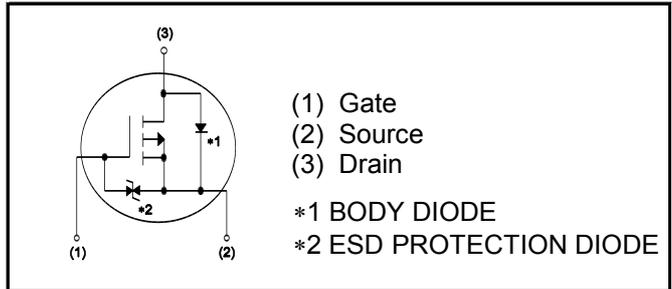
●Application

DC/DC converters

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TL
	Marking	ZH

●Absolute maximum ratings($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-45	V
Continuous drain current	I_D^{*1}	±2.0	A
Pulsed drain current	$I_{D,pulse}^{*2}$	±8.0	A
Gate - Source voltage	V_{GSS}	±20	V
Power dissipation	P_D^{*3}	1.0	W
	P_D^{*4}	0.54	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	125	°C/W
	R_{thJA}^{*4}	-	-	232	°C/W

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-45	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1mA$ referenced to 25°C	-	-43	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -45V, V_{GS} = 0V$	-	-	-1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0	-	-3.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	$I_D = -1mA$ referenced to 25°C	-	3.2	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = -10V, I_D = -2.0A$	-	130	190	mΩ
		$V_{GS} = -4.5V, I_D = -2.0A$	-	180	260	
		$V_{GS} = -4.0V, I_D = -2.0A$	-	200	280	
		$V_{GS} = -10V, I_D = -2.0A, T_j = 125^\circ\text{C}$	-	200	280	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	21	-	Ω
Transconductance	g_{fs}^{*5}	$V_{DS} = -10V, I_D = -2.0A$	1.2	4.0	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (12×20×0.8mm)

*5 Pulsed

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$	-	500	-	pF
Output capacitance	C_{oss}	$V_{DS} = -10\text{V}$	-	80	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	40	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx -25\text{V}, V_{GS} = -10\text{V}$	-	8	-	ns
Rise time	t_r^{*5}	$I_D = -1.0\text{A}$	-	10	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 25\Omega$	-	35	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	10	-	

●Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx -25\text{V}, I_D = -2.0\text{A}$ $V_{GS} = -4.5\text{V}$	-	4.5	-	nC
		$V_{DD} \approx -25\text{V}, I_D = -2.0\text{A}$ $V_{GS} = -10\text{V}$	-	9.5	-	
Gate - Source charge	Q_{gs}^{*5}	$V_{DD} \approx -25\text{V}, I_D = -2.0\text{A}$	-	1.6	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = -10\text{V}$	-	1.2	-	

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_a = 25^\circ\text{C}$	-	-	-0.8	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = -2.0\text{A}$	-	-	-1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

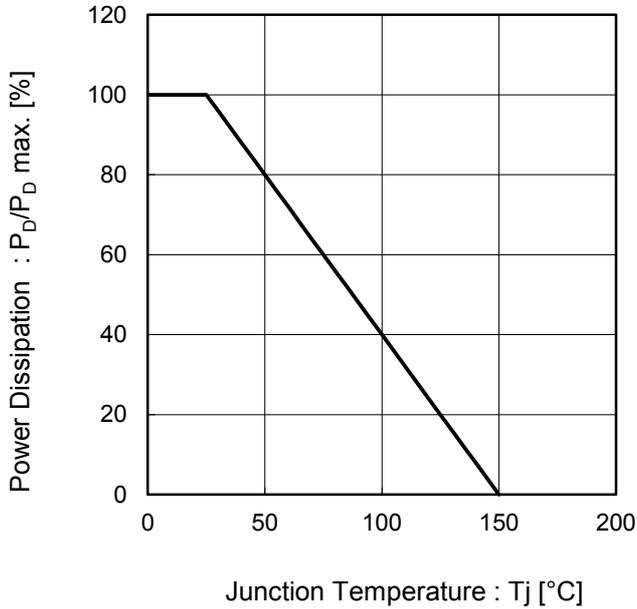


Fig.2 Maximum Safe Operating Area

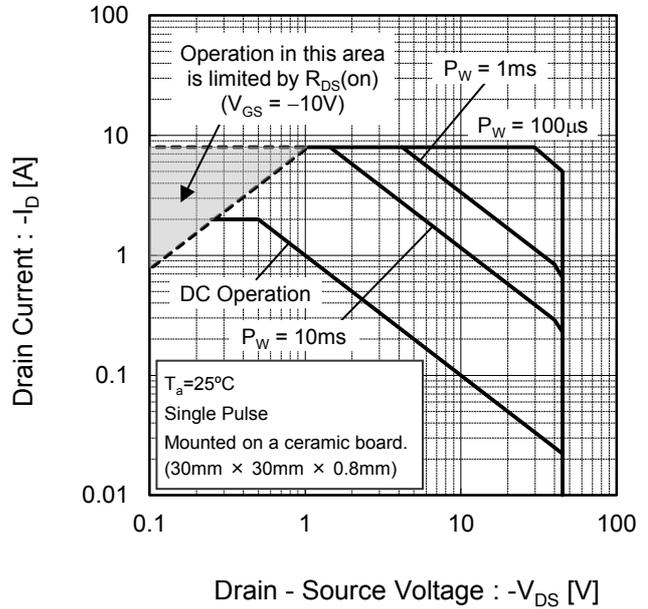


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

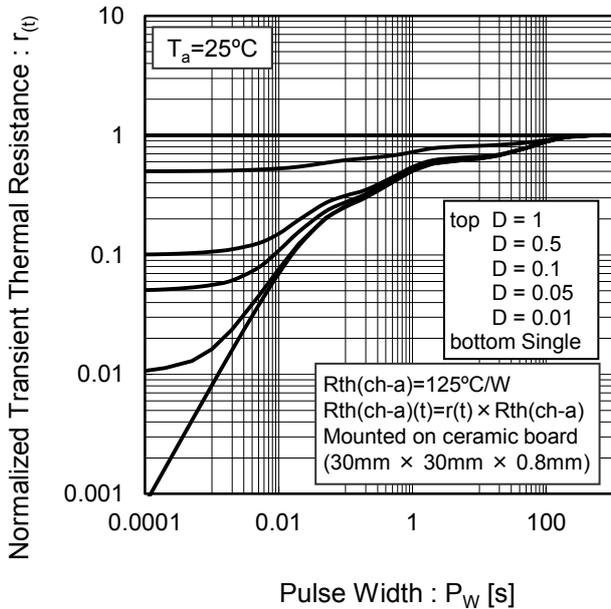
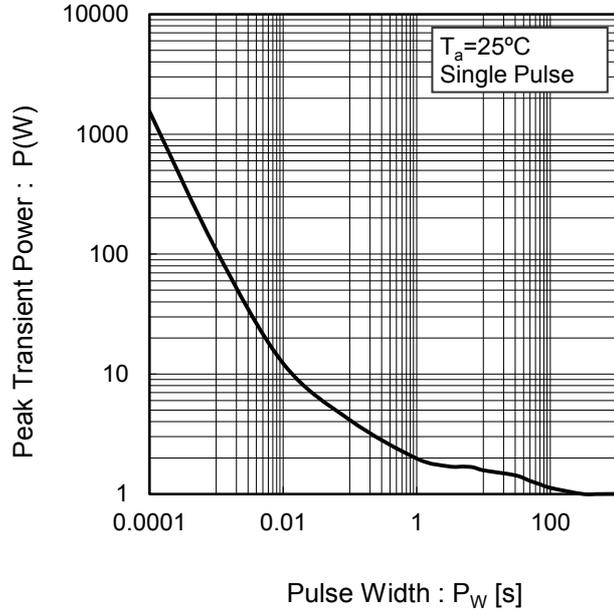


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

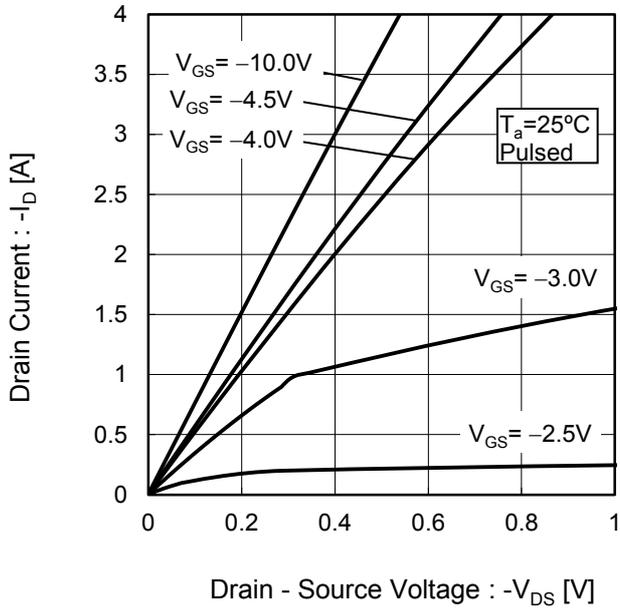


Fig.6 Typical Output Characteristics(II)

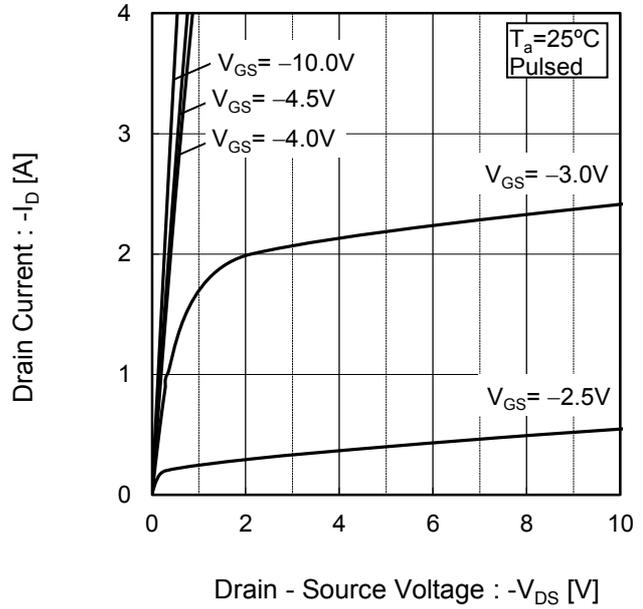


Fig.7 Breakdown Voltage vs. Junction Temperature

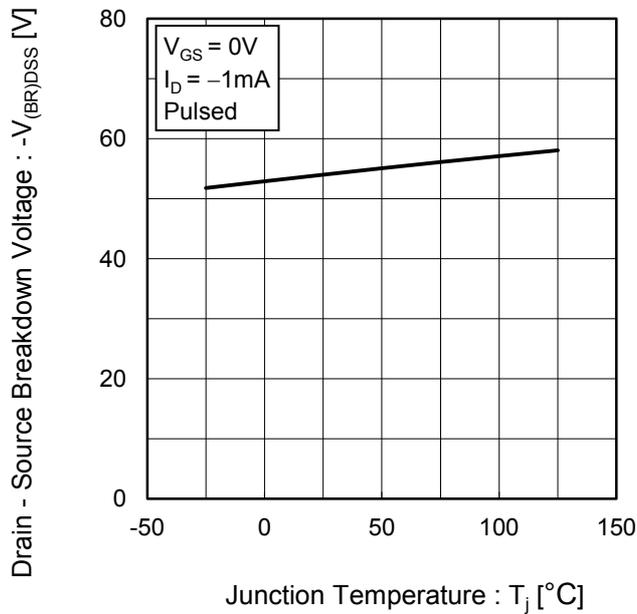
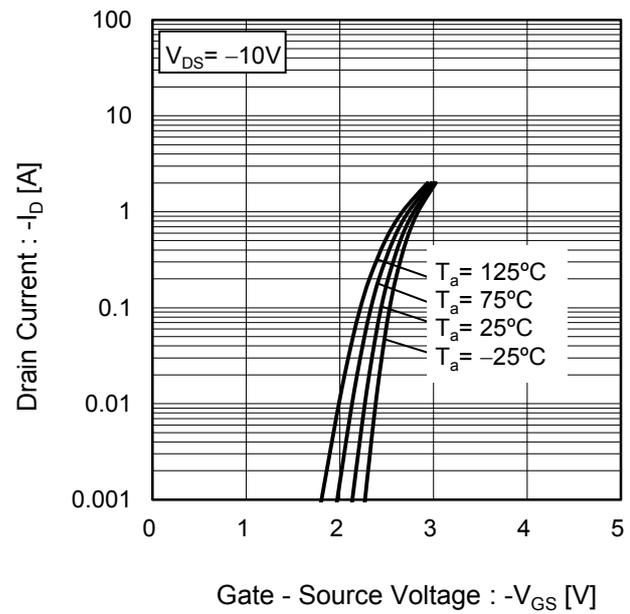


Fig.8 Typical Transfer Characteristics



●Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

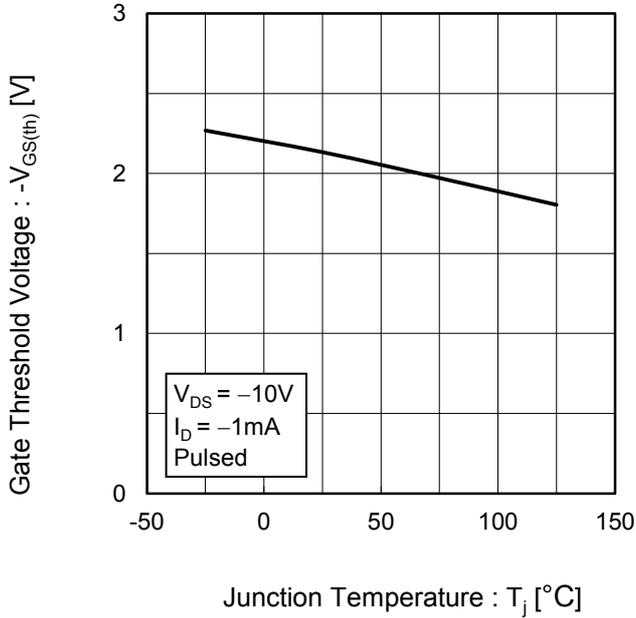


Fig.10 Transconductance vs. Drain Current

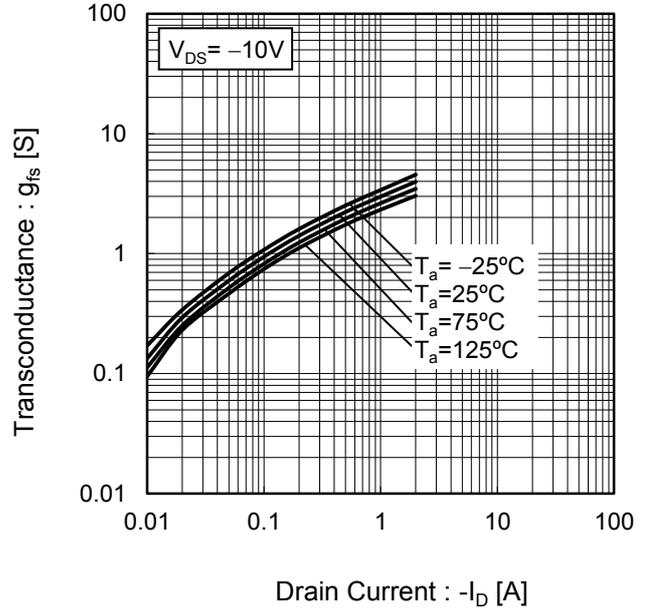


Fig.11 Drain Current Derating Curve

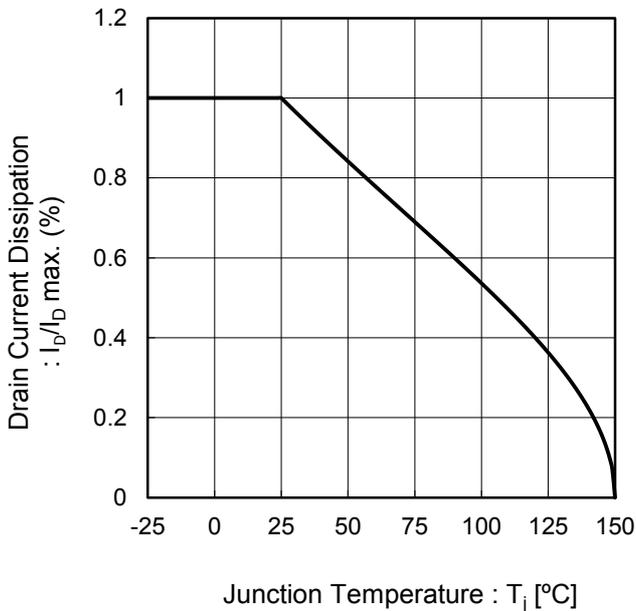
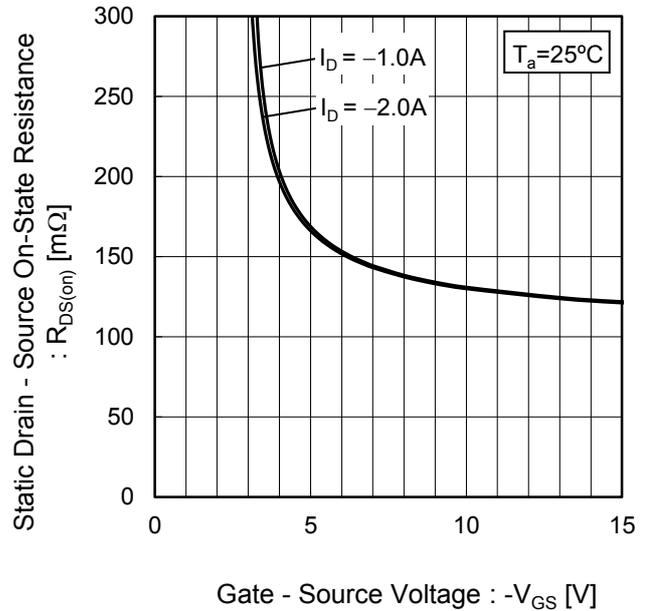


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

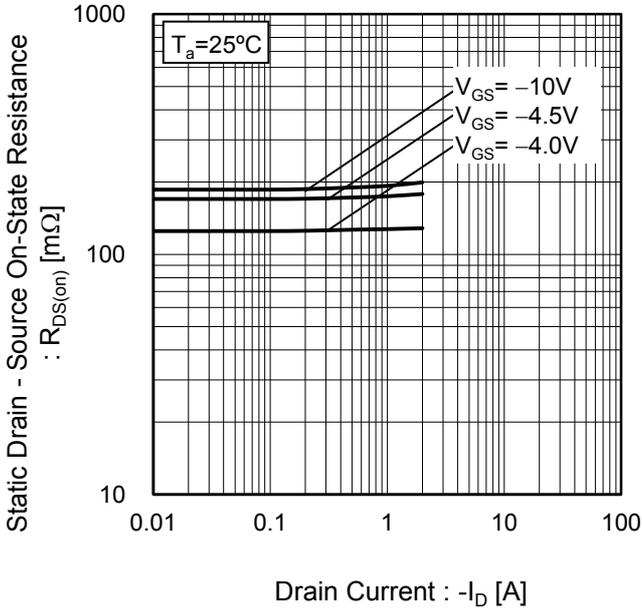


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

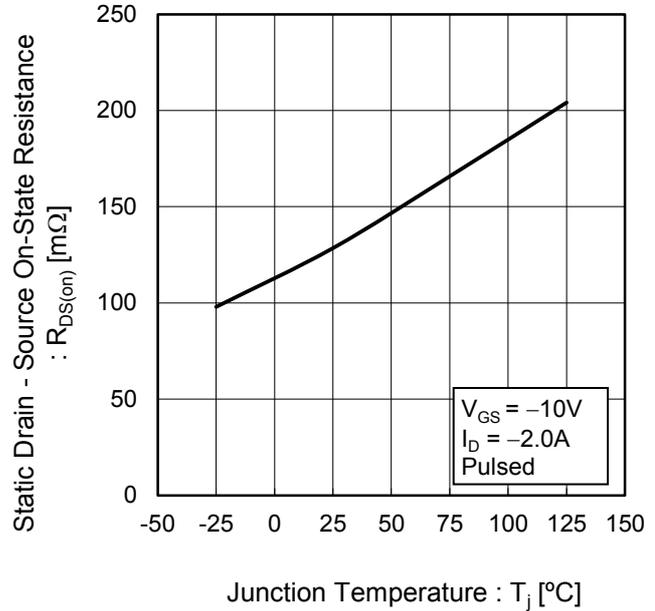


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

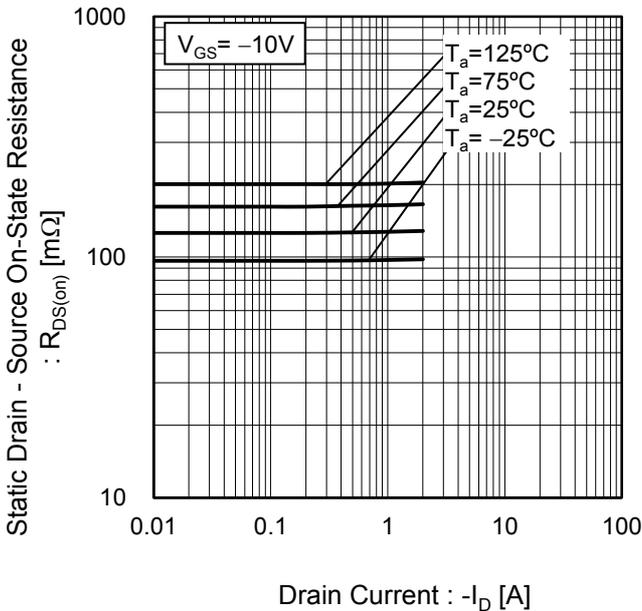
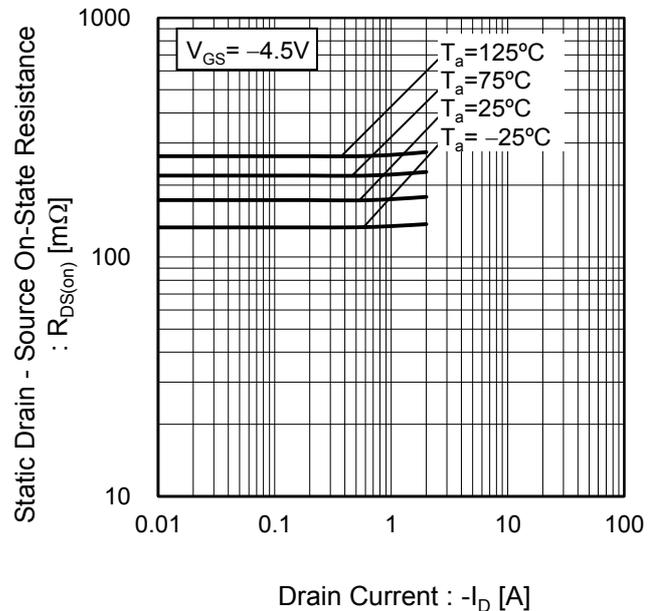


Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)



●Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

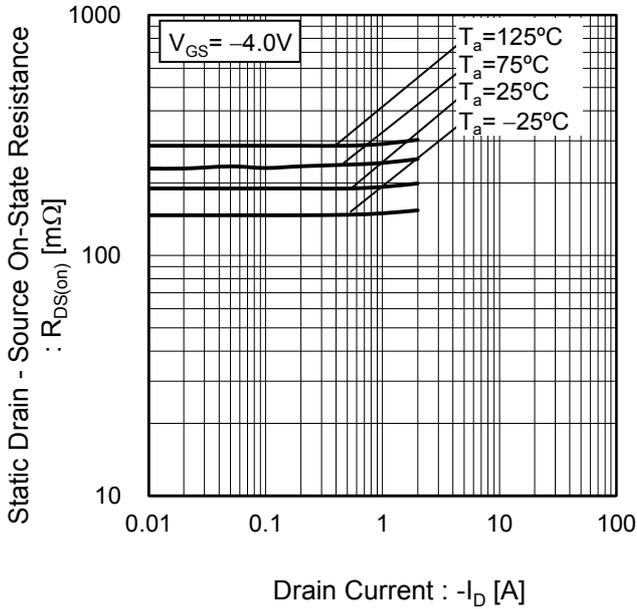


Fig.18 Typical Capacitance vs. Drain - Source Voltage

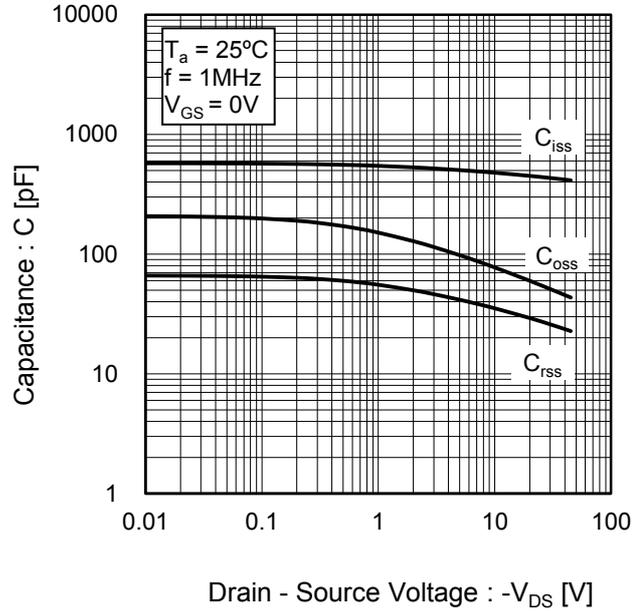


Fig.19 Switching Characteristics

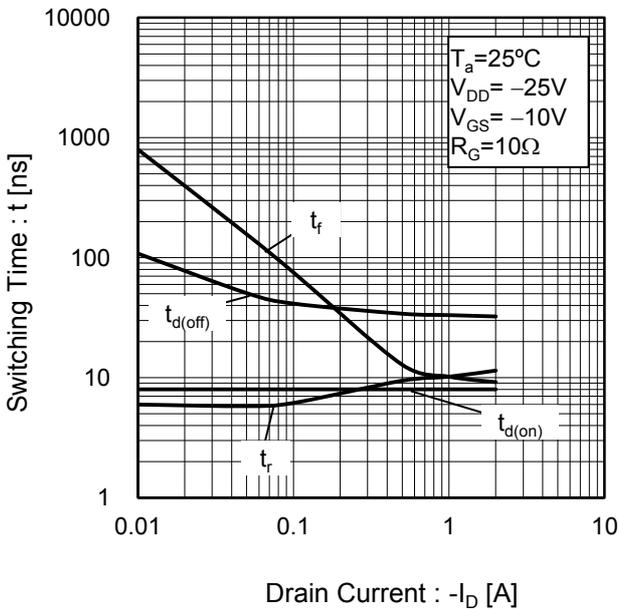
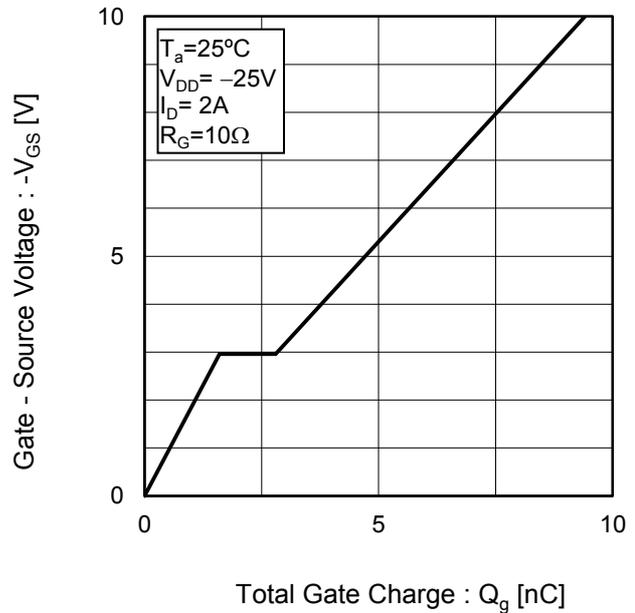
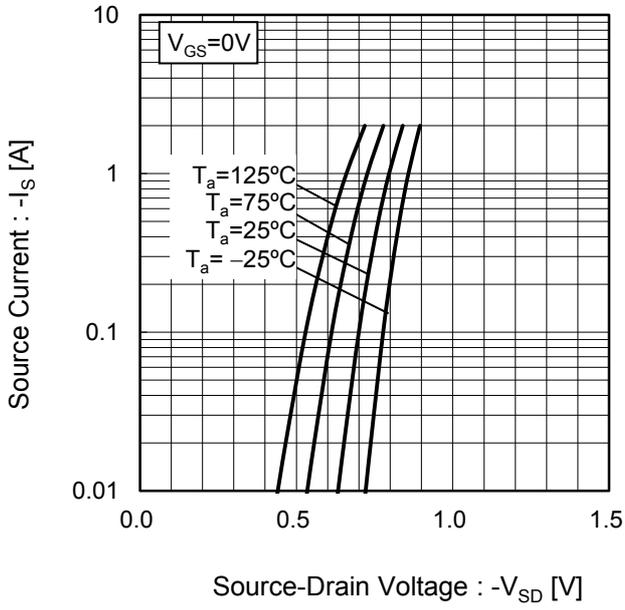


Fig.20 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.21 Source Current vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

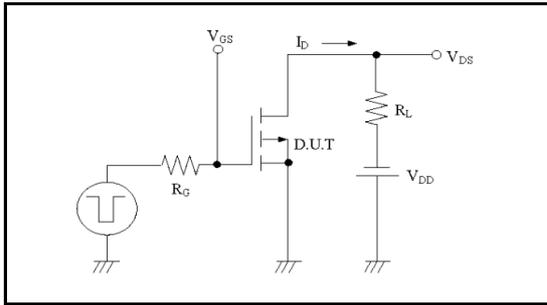


Fig.1-2 Switching Waveforms

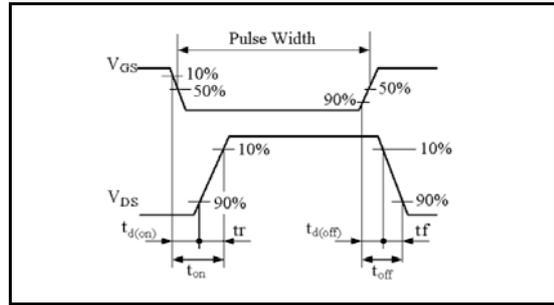


Fig.2-1 Gate Charge Measurement Circuit

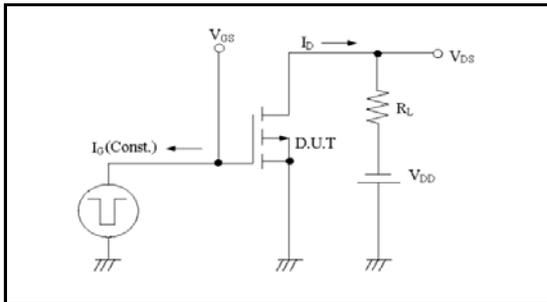
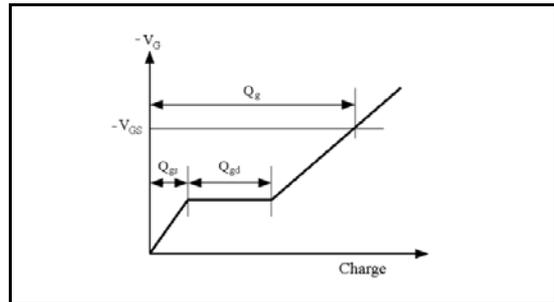
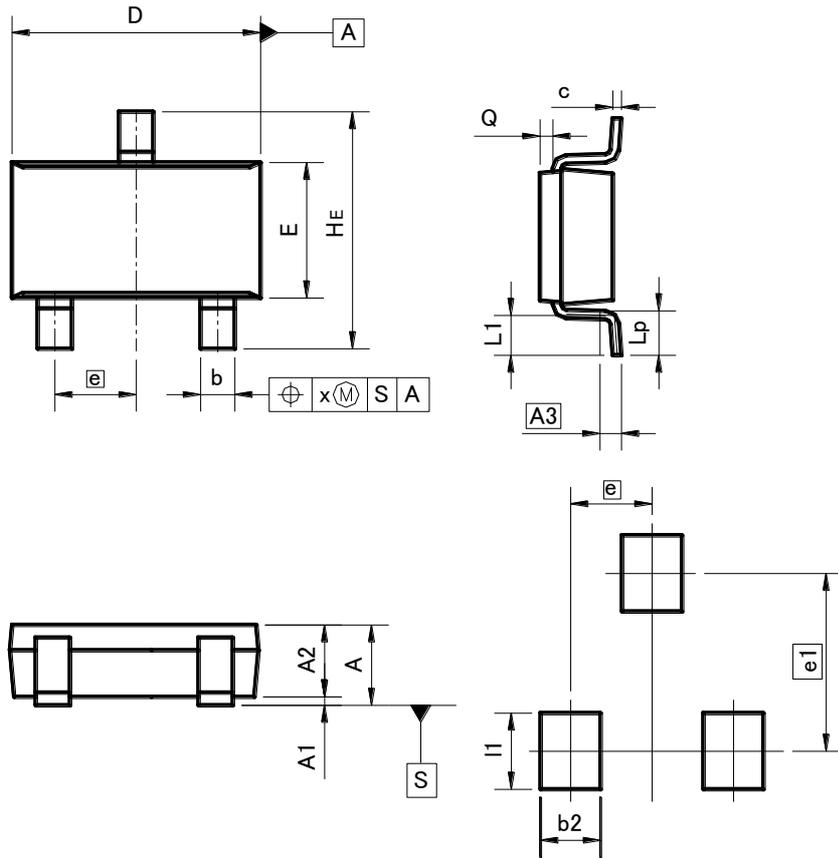


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)

TSMT3



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.00	-	0.039
A1	0.00	0.10	0	0.004
A2	0.75	0.95	0.03	0.037
A3	0.25		0.01	
b	0.35	0.50	0.014	0.02
c	0.10	0.26	0.004	0.01
D	2.80	3.00	0.11	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.04	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.01
x	-	0.20	-	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	2.10		0.08	
b2	-	0.70	-	0.028
l1	-	0.90	-	0.035

Dimension in mm/inches